

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7741	438/184,230,265,300,301,303-307,356,563,592,595,596,663,664.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 09:46
L3	54	1 and ((elevat\$3 near (source drain)) same ((epitaxial epi) near (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:07
L4	11	1 and ((deep near (source drain)) same ((epitaxial epi) near (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:08
L5	326	1 and (deep near (source drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:07
L6	68	5 and ((epitaxial epi) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:02
L7	69	5 and ((epi\$6 epi) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:02
L8	142	((elevat\$3 near (source drain)) same ((epitaxial epi) near (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:07
L9	19	8 and (deep near (source drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:07
L10	50	((deep near (source drain)) same ((epitaxial epi) near (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 10:11

L11	12	(method process\$3) AND (((metal near oxide) MOS) near transistor\$1) AND (elevat\$3 near (source drain)) AND (gate near (electrode dielectric oxide insulat\$3 spacer)) AND (epi\$6 near (layer film)) AND implant\$3 AND ((source drain) near (extension deep)).CLM.	US-PGPUB; USPAT	OR	ON	2005/11/10 10:16
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